

What is claimed is:

1. A spin valve head comprising:
  - a first pinned magnetic layer;
  - a non-magnetic layer being formed on said first pinned magnetic layer; and
  - a second pinned magnetic layer being formed on said non-magnetic layer,characterized by,
  - an insulating specular layer being provided between said first pinned magnetic layer and said second pinned magnetic layer.
2. The spin valve head according to claim 1,
  - wherein said insulating specular layer is provided between said non-magnetic layer and said second pinned magnetic layer.
3. The spin valve head according to claim 1,
  - wherein said insulating specular layer is made of an oxide of an alloy including at least one of CO, Ni and Fe.
4. The spin valve head according to claim 1,
  - wherein thickness of said insulating specular layer is 0.6-1.0 nm.
5. The spin valve head according to claim 1,
  - wherein said insulating specular layer is an oxide film, which is formed by oxidizing a metal layer.
6. The spin valve head according to claim 1,
  - wherein said insulating specular layer is a metal oxide film formed, on

said non-magnetic layer, by a film forming process.

7. The spin valve head according to claim 3,

wherein said insulating specular layer is formed by forming a film of the oxide on said non-magnetic layer in a chamber and introducing oxygen into the chamber to stick oxygen onto a surface of the non-magnetic oxide film.

8. The spin valve head according to claim 5,

wherein the metal layer is oxidized by a process selected from natural oxidization, plasma oxidization and ion beam oxidization.

9. The spin valve head according to claim 6,

wherein the film forming process is selected from sputtering, evaporation and CVD.

10. A magnetic recording device,

having a magnetic head section for reproducing data recorded on a magnetic recording medium,

wherein said magnetic head section including a spin valve head comprising:

a first pinned magnetic layer;

a non-magnetic layer being formed on said first pinned magnetic layer; and

a second pinned magnetic layer being formed on said non-magnetic layer,

characterized by,

an insulating specular layer being provided between said first pinned magnetic layer and said second pinned magnetic layer.

11. The device according to claim 10,  
wherein said insulating specular layer is provided between said non-magnetic layer and said second pinned magnetic layer.
12. The device according to claim 10,  
wherein said insulating specular layer is made of an oxide of an alloy including at least one of CO, Ni and Fe.
13. The device according to claim 10,  
wherein thickness of said insulating specular layer is 0.6-1.0 nm.
14. The device according to claim 10,  
wherein said insulating specular layer is an oxide film, which is formed by oxidizing a metal layer.
15. The device according to claim 10,  
wherein said insulating specular layer is a metal oxide film formed, on said non-magnetic layer, by a film forming process.
16. The device according to claim 12,  
wherein said insulating specular layer is formed by forming a film of the oxide on said non-magnetic layer in a chamber and introducing oxygen into the chamber to stick oxygen onto a surface of the non-magnetic oxide film.
17. The device according to claim 14,  
wherein the metal layer is oxidized by a process selected from natural oxidization, plasma oxidization and ion beam oxidization.

18. The device according to claim 15,  
wherein the film forming process is selected from sputtering,  
evaporation and CVD.